

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS395

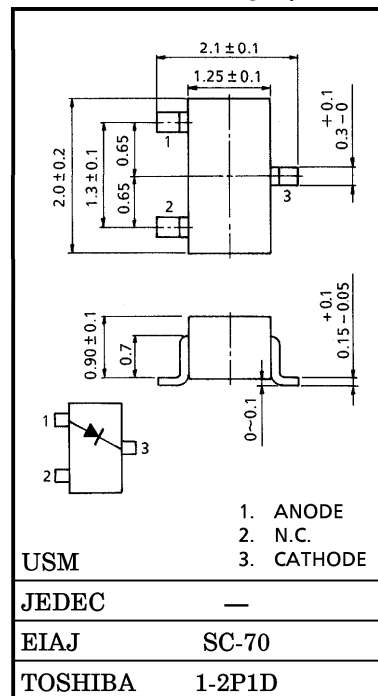
HIGH SPEED SWITCHING APPLICATION

Unit in mm

- Small Package
- Low Forward Voltage : $V_F(2) = 0.23V$ (Typ.) @ $I_F = 5mA$

MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|--------------------------------|-----------|---------|------|
| Maximum (Peak) Reverse Voltage | V_{RM} | 15 | V |
| Reverse Voltage | V_R | 10 | V |
| Maximum (Peak) Forward Current | I_{FM} | 200 | mA |
| Average Forward Current | I_O | 100 | mA |
| Surge Current (10ms) | I_{FSM} | 1 | A |
| Power Dissipation | P | 100 | mW |
| Junction Temperature | T_j | 125 | °C |
| Storage Temperature Range | T_{stg} | -55~125 | °C |
| Operating Temperature Range | T_{opr} | -40~100 | °C |



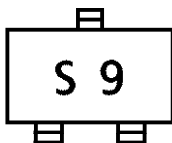
Weight : 0.006g

※ Unit Rating. Total Rating=Unit Rating×0.7

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|-------------------|----------|---------------------|------|------|------|---------|
| Forward Voltage | $V_F(1)$ | $I_F = 1mA$ | — | 0.18 | — | V |
| | $V_F(2)$ | $I_F = 5mA$ | — | 0.23 | 0.30 | |
| | $V_F(3)$ | $I_F = 100mA$ | — | 0.35 | 0.50 | |
| Reverse Current | I_R | $V_R = 10V$ | — | — | 20 | μA |
| Total Capacitance | C_T | $V_R = 0, f = 1MHz$ | — | 20 | 40 | pF |

MARKING



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